# NPN Silicon Planar Epitaxial Transistor

This NPN Silicon Epitaxial transistor is designed for use in industrial and consumer applications. The device is housed in the SOT–223 package which is designed for medium power surface mount applications.

SOT-223 package ensures level mounting, resulting in improved thermal conduction, and allows visual inspection of soldered joints. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die.

## Features

- High Current
- The SOT-223 Package can be Soldered Using Wave or Reflow
- PNP Complement is PZT751T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

## MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	60	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector Current	Ι <sub>C</sub>	2.0	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	0.8 6.4	W mW/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to 150	°C
Junction Temperature	TJ	150	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance from Junction-to-Ambient in Free Air	$R_{\thetaJA}$	156	°C/W
Maximum Temperature for Soldering Purposes	ΤL	260	°C
Time in Solder Bath		10	Sec

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.



## **ON Semiconductor®**

www.onsemi.com

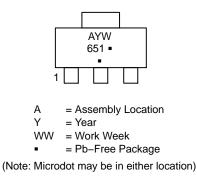
## SOT-223 PACKAGE HIGH CURRENT NPN SILICON TRANSISTOR SURFACE MOUNT





EMITTER 3

## MARKING DIAGRAM



## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
PZT651T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT651T1G	SOT–223 (Pb–Free)	1,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **PZT651**

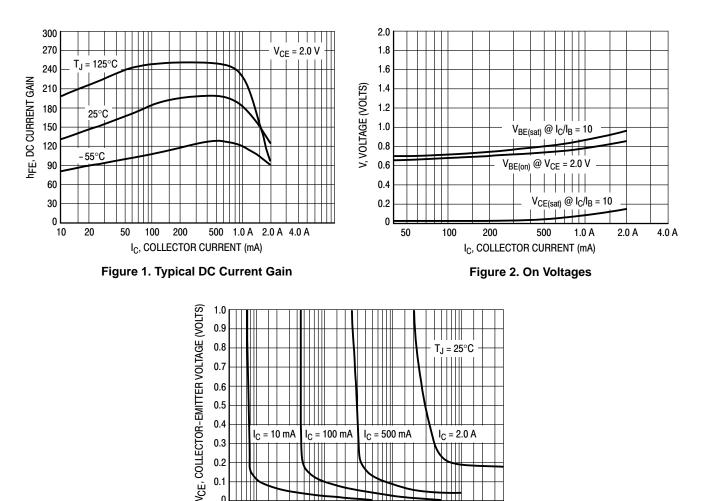
## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage $(I_C = 10 \text{ mAdc}, I_B = 0)$	V <sub>(BR)CEO</sub>	60	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = 100 \ \mu Adc, I_E = 0)$	V <sub>(BR)</sub> CBO	80	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V <sub>(BR)EBO</sub>	5.0	_	Vdc
Base–Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc)	I <sub>EBO</sub>	_	0.1	μAdc
Collector–Base Cutoff Current ( $V_{CB} = 80 \text{ Vdc}, I_E = 0$ )	I <sub>CBO</sub>	_	100	nAdc
ON CHARACTERISTICS (Note 2)				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_C = 50 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 500 \text{ mAdc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 1.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}) \\ (I_C = 2.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}) \end{array} $	h <sub>FE</sub>	75 75 75 40	- - - -	_
Collector–Emitter Saturation Voltages ( $I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc}$ ) ( $I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc}$ )	V <sub>CE(sat)</sub>		0.5 0.3	Vdc
Base–Emitter Voltages ( $I_C = 1.0 \text{ Adc}, V_{CE} = 2.0 \text{ Vdc}$ )	V <sub>BE(on)</sub>	_	1.0	Vdc
Base–Emitter Saturation Voltage $(I_C = 1.0 \text{ Adc}, I_B = 100 \text{ mAdc})$	V <sub>BE(sat)</sub>	_	1.2	Vdc
Current–Gain — Bandwidth ( $I_C = 50$ mAdc, $V_{CE} = 5.0$ Vdc, f = 100 MHz)	fT	75	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle = 2.0%

## **PZT651**

## **TYPICAL CHARACTERISTICS**



0.4

0.3 0.2 0.1

0

0.05 0.1 0.2

I<sub>C</sub> = 10 mA

I<sub>C</sub> = 100 mA

0.5 1.0 2.0

I<sub>C</sub> = 500 mA

ШГ

IB, BASE CURRENT (mA) Figure 3. Collector Saturation Region

5.0 10 20

I<sub>C</sub> = 2.0 Å

50 100 200 500

DATE 02 OCT 2018

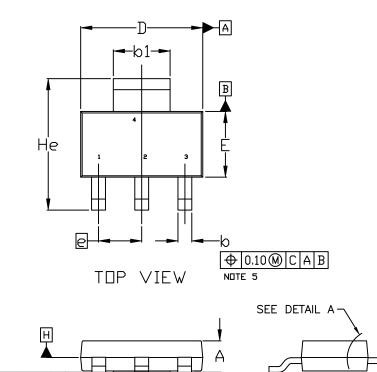




SCALE 1:1

0.10 C

A1



-11

SIDE VIEW

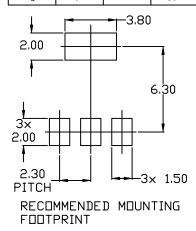
DETAIL A

NDTES:

SOT-223 (TO-261) CASE 318E-04 ISSUE R

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST PDINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS			
DIM	MIN.	NDM.	MAX.	
A	1.50	1.63	1.75	
A1	0.02	0.06	0.10	
b	0.60	0.75	0.89	
b1	2.90	3.06	3.20	
с	0.24	0.29	0.35	
D	6.30	6.50	6.70	
E	3.30	3.50	3.70	
e	2.30 BSC			
L	0.20			
L1	1.50	1.75	2.00	
He	6.70	7.00	7.30	
θ	0*		10*	



DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-223 (TO-261)		PAGE 1 OF 2	
ON Semiconductor and 💷 are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries.				

FRONT VIEW

ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2018

#### SOT-223 (TO-261) CASE 318E-04 ISSUE R

#### DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	Style 9: Pin 1. Input 2. Ground 3. Logic 4. Ground	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	Style 12: Pin 1. Input 2. Output 3. NC 4. Output	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

## GENERIC MARKING DIAGRAM\*



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package
- (Note: Microdot may be in either location) \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42680B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SOT-223 (TO-261)		PAGE 2 OF 2	
ON Semiconductor and (1) are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the output further notice to any products herein. ON semiconductor makes no warranty, representation or guarantee regarding the output for the				

the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and calcular performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

#### TECHNICAL SUPPORT

onsemi Website: www.onsemi.com

Email Requests to: orderlit@onsemi.com

North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative